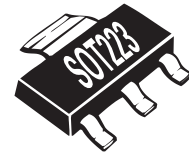


ZXM64P035G

35V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -35V$; $R_{DS(on)} = 0.075\Omega$; $I_D = -5.3A$



DESCRIPTION

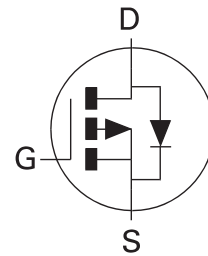
This new generation of high cell density planar MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

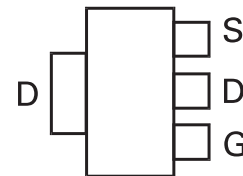
APPLICATIONS

- 50W Class D Audio Output Stage
- Motor Control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM64P035GTA	7"	12mm	1000 units
ZXM64P035GTC	13"	12mm	4000 units



Top View

DEVICE MARKING

- ZXM6
4P035

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ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-35	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (V _{GS} = -10V; T _A =25°C)(b) (V _{GS} = -10V; T _A =70°C)(b) (V _{GS} = -10V; T _A =25°C)(a)	I _D	-5.3 -4.3 -3.8	A
Pulsed Drain Current (c)	I _{DM}	-19	A
Continuous Source Current (Body Diode) (b)	I _S	-2.3	A
Pulsed Source Current (Body Diode)(c)	I _{SM}	-19	A
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	2.0 16	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	3.9 31	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R _{θJA}	62.5	°C/W
Junction to Ambient (b)	R _{θJA}	32	°C/W

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at t≤10 secs.
- (c) Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width limited by maximum junction temperature.



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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

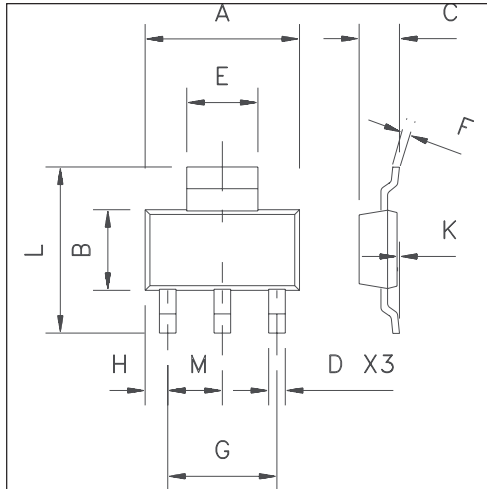
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-35			V	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	$V_{DS} = -35\text{V}$, $V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}			± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.075 0.105	Ω Ω	$V_{GS} = -10\text{V}$, $I_D = -2.4\text{A}$ $V_{GS} = -4.5\text{V}$, $I_D = -1.2\text{A}$
Forward Transconductance (1)(3)	g_{fs}	2.3			S	$V_{DS} = -10\text{V}$, $I_D = -1.2\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		825		pF	$V_{DS} = -25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{oss}		250		pF	
Reverse Transfer Capacitance	C_{rss}		80		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		4.4		ns	$V_{DD} = -15\text{V}$, $I_D = -2.4\text{A}$ $R_G = 6.0\Omega$, $V_{GS} = -10\text{V}$
Rise Time	t_r		6.2		ns	
Turn-Off Delay Time	$t_{d(off)}$		40		ns	
Fall Time	t_f		29.2		ns	
Total Gate Charge	Q_g			46	nC	$V_{DS} = -24\text{V}$, $V_{GS} = -10\text{V}$, $I_D = -2.4\text{A}$
Gate-Source Charge	Q_{gs}			9	nC	
Gate-Drain Charge	Q_{gd}			11.5	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	$T_J = 25^\circ\text{C}$, $I_S = -2.4\text{A}$, $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	t_{rr}		30.2		ns	$T_J = 25^\circ\text{C}$, $I_F = -2.4\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		27.8		nC	

NOTES

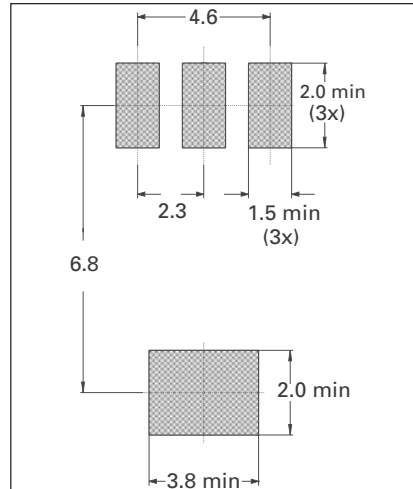
- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

ZXM64P035G

PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	6.3	6.7	0.248	0.264
B	3.3	3.7	0.130	0.146
C	-	1.7	-	0.067
D	0.6	0.8	0.024	0.031
E	2.9	3.1	0.114	0.122
F	0.24	0.32	0.009	0.13
G	NOM 4.6		NOM 0.181	
H	0.85	1.05	0.033	0.041
K	0.02	0.10	0.0008	0.004
L	6.7	7.3	0.264	0.287
M	NOM 2.3		NOM 0.0905	

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